

60 V, N-channel Trench MOSFET

7 May 2019

### 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Logic-level compatible
- Extended temperature range T<sub>i</sub> = 175 °C
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM (class H2)
- AEC-Q101 qualified

#### 3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

#### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	60	V
V <sub>GS</sub>	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	2.2	А
Static chara	acteristics						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 2.2 A; T <sub>j</sub> = 25 °C		-	88	117	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

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### 5. Pinning information

Table 2. F	Table 2. Pinning information							
Pin	Symbol	Description	Simplified outline	Graphic symbol				
1	G	gate	3	D				
2	S	source						
3	D	drain	1 2 TO-236AB (SOT23)	G S 017aaa255				

### 6. Ordering information

Table 3. Ordering information						
Type number Package						
	Name	Description	Version			
PMV88ENEA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

### 7. Marking

#### Table 4. Marking codes

Type number	Marking code[1]
PMV88ENEA	HT%

[1] % = placeholder for manufacturing site code

#### 8. Limiting values

#### Table 5. Limiting values

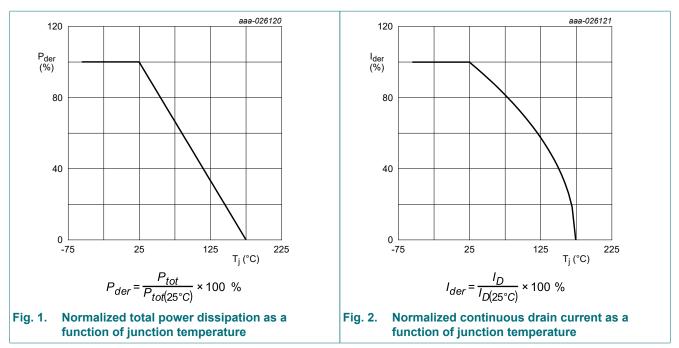
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	60	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	2.2	А
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	1.6	А
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	8.9	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	615	mW
			[1]	-	1.26	W
		T <sub>sp</sub> = 25 °C		-	7.5	W
Tj	junction temperature			-55	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C
Source-drain	n diode					
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	1.3	А
ESD maximu	um rating			I		
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	2000	V
Avalanche r	uggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 0.25 A; DUT in avalanche (unclamped)		-	8	mJ
	1					

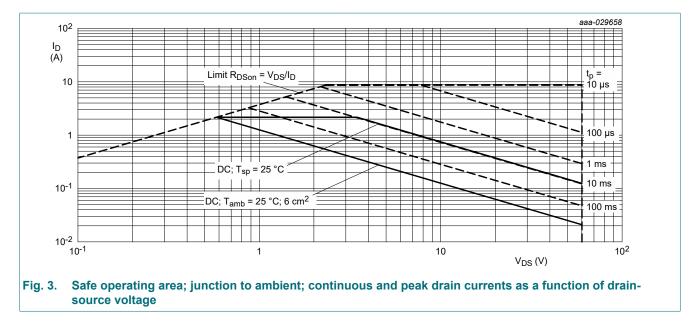
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.



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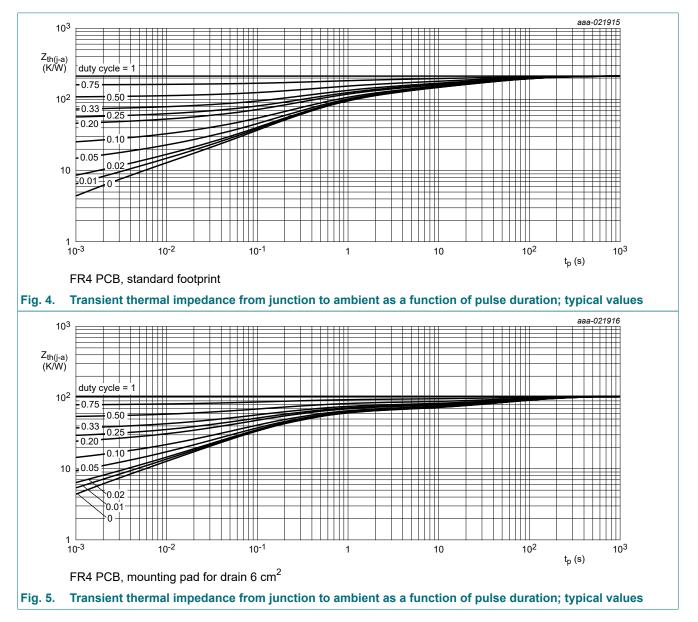


### 9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from	in free air	[1]	-	212	244	K/W
	junction to ambient		[2]	-	104	119	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	17	20	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

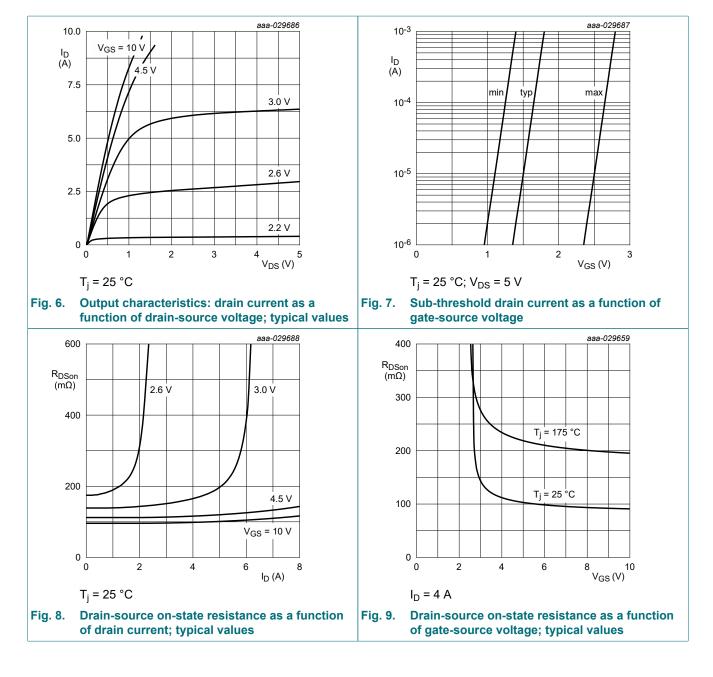
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



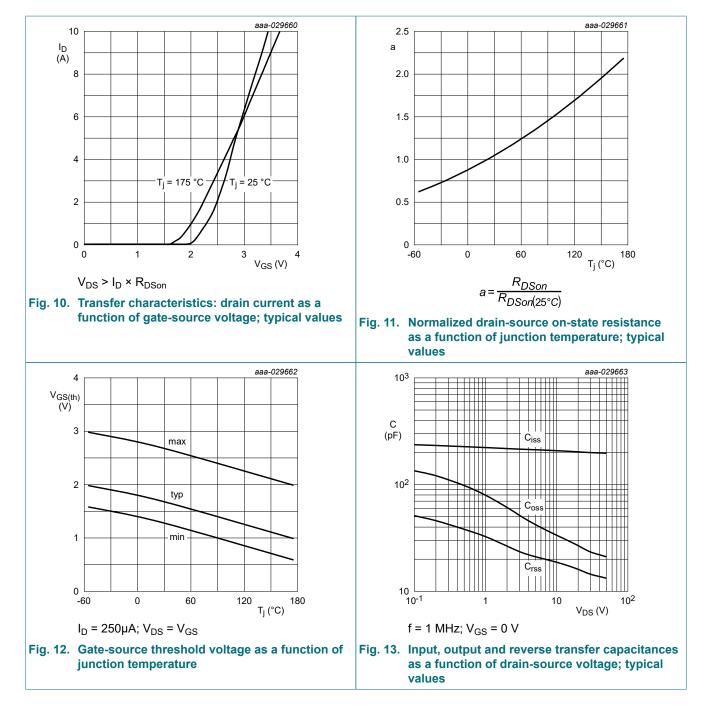
### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	60	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	$I_D = 250 \ \mu A; V_{DS} = V_{GS}; T_j = 25 \ ^{\circ}C$	1.3	1.7	2.7	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 2.2 A; T <sub>j</sub> = 25 °C	-	88	117	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 2.2 A; T <sub>j</sub> = 175 °C	-	191	254	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 2 A; T <sub>j</sub> = 25 °C	-	104	146	mΩ
9fs	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 2 A; T <sub>j</sub> = 25 °C	-	8.5	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz	-	10	-	Ω
Dynamic ch	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 30 V; I <sub>D</sub> = 2.2 A; V <sub>GS</sub> = 10 V;	-	4	6	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.5	-	nC
Q <sub>GD</sub>	gate-drain charge		-	0.9	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 30 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	196	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	24	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	15	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 30 V; I <sub>D</sub> = 2.2 A; V <sub>GS</sub> = 10 V;	-	3	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	6	-	ns
t <sub>d(off)</sub>	turn-off delay time	1 [	-	8	-	ns
t <sub>f</sub>	fall time	1	-	3	-	ns
Source-drai	n diode					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 1.3 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 0.8 A; dI <sub>S</sub> /dt = -100 A/µs;	-	11	-	ns
Q <sub>r</sub>	recovered charge	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 30 V; T <sub>j</sub> = 25 °C	-	4	-	nC

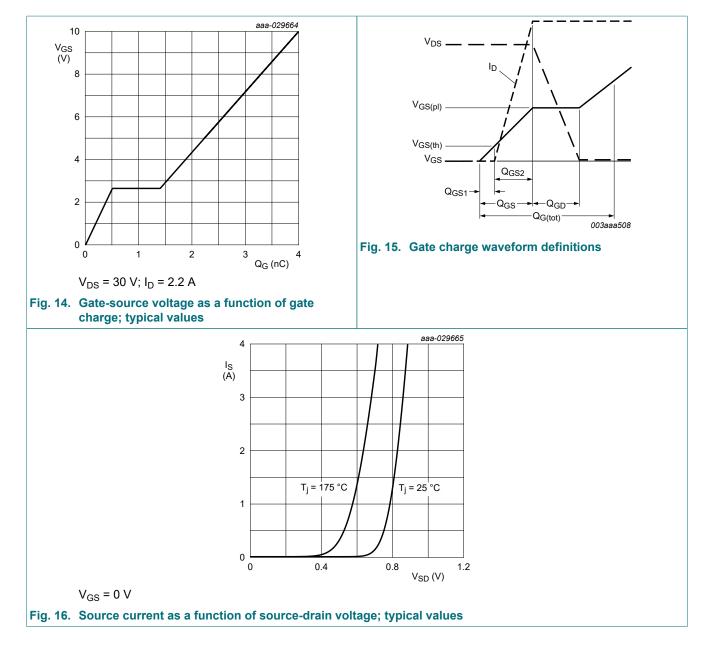
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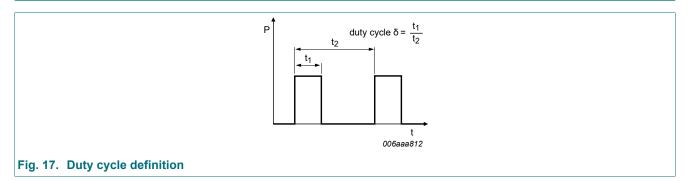
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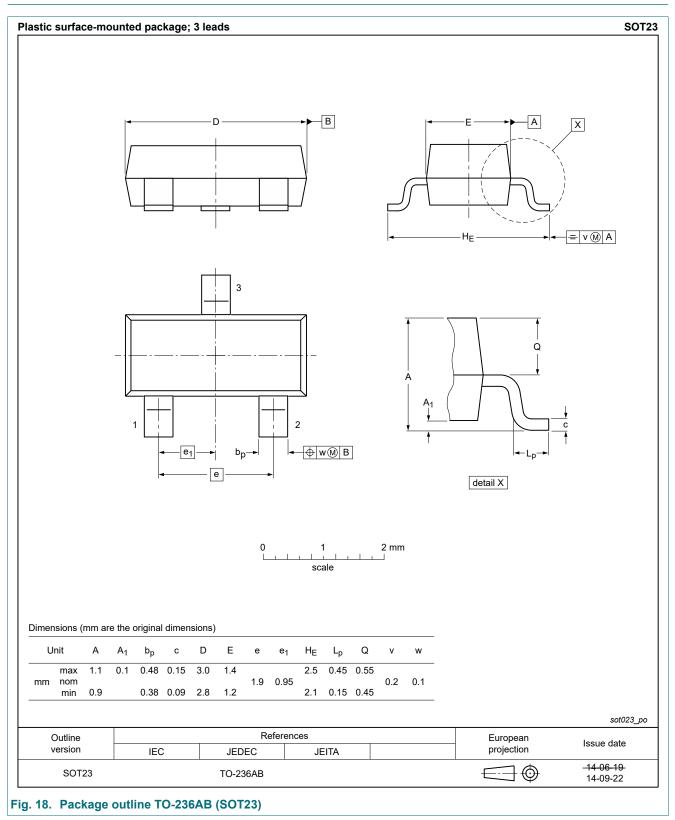
### **11. Test information**



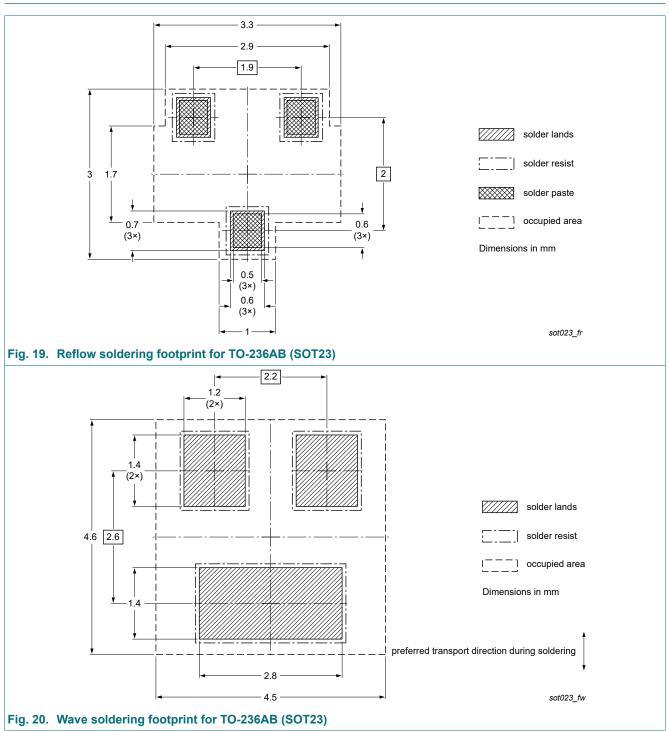
#### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 12. Package outline



### 13. Soldering



### 14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMV88ENEA v.1	20190507	Product data sheet	-	-		

### 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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**Product data sheet** 

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